

**Absolute Maximum Ratings**

Symbol	Parameter	Value					Unit	
		Qxx04LT	Qxx06LT / Qxx06LTH	Qxx08LT / Qxx08LTH	Qxx10LT / Qxx10LTH	Qxx15LT / Qxx15LTH		
$I_{T(RMS)}$	RMS forward current	Qxx04LT: $T_C = 95^\circ\text{C}$ Qxx06LT/Qxx08LT/Qxx10LT: $T_C = 90^\circ\text{C}$ Qxx15LT: $T_C = 80^\circ\text{C}$					A	
$I_{TSM}$	Peak non-repetitive surge current	single half cycle; $f = 50\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$	46	65	83	100	167	A
		single half cycle; $f = 60\text{Hz}$ ; $T_J$ (initial) = $25^\circ\text{C}$	55	80	100	120	200	
$I^2t$	$I^2t$ value for fusing	$t_o = 8.3\text{ms}$	12.5	26.5	41	60	166	$\text{A}^2\text{s}$
$di/dt$	Critical rate-of-rise of on-state current	$f = 60\text{Hz}$ ; $T_J = 125^\circ\text{C}$	50	70		100		$\text{A}/\mu\text{s}$
$I_{GM}$	Peak gate current	$T_J = 125^\circ\text{C}$	1.5					A
$T_{stg}$	Storage temperature range		-40 to 150					$^\circ\text{C}$
$T_J$	Operating junction temperature range		-40 to 125					$^\circ\text{C}$

Note: xx = voltage

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) – Standard Quadrac**

Symbol	Test Conditions		Value					Unit	
			Qxx04LT	Qxx06LT	Qxx08LT	Qxx10LT	Qxx15LT		
$I_H$	$I_T = 200\text{mA}$ (initial)	MAX.	40	50	60	60	70	mA	
$dv/dt$	$V_D = V_{DRM}$ ; gate open; $T_J = 100^\circ\text{C}$	MIN.	400V	75	150	175	200	300	$\text{V}/\mu\text{s}$
			600V	50	125	150	175	200	
	$V_D = V_{DRM}$ ; gate open; $T_J = 125^\circ\text{C}$	MIN.	400V	50	100	120	150	200	
			600V	50	85	100	120	150	
$dv/dt(c)$	$di/dt(c) = 0.54 \times I_{T(RMS)} / \text{ms}$ ; $T_J = 125^\circ\text{C}$	MIN.	3	4				$\text{V}/\mu\text{s}$	
$t_{gt}$	(note 1)	TYP.	3					$\mu\text{s}$	

(1) Reference test circuit in figure 10 and waveform in figure 11;  $C_T = 0.1\mu\text{F}$  with  $0.1\mu\text{s}$  rise time.  
Note: xx = voltage

**Electrical Characteristics ( $T_J = 25^\circ\text{C}$ , unless otherwise specified) – Alternistor Quadrac**

Symbol	Test Conditions		Value				Unit	
			Qxx06LTH	Qxx08LTH	Qxx10LTH	Qxx15LTH		
$I_H$	$I_T = 20\text{mA}$ (initial)	MAX.	50	50	60	70	mA	
$dv/dt$	$V_D = V_{DRM}$ ; gate open; $T_J = 100^\circ\text{C}$	MIN.	400V	575		925		$\text{V}/\mu\text{s}$
			600V	425		775		
	$V_D = V_{DRM}$ ; gate open; $T_J = 125^\circ\text{C}$	MIN.	400V	450		700		
			600V	350		600		
$dv/dt(c)$	$di/dt(c) = 0.54 \times I_{T(RMS)} / \text{ms}$ ; $T_J = 125^\circ\text{C}$	MIN.	25		30		$\text{V}/\mu\text{s}$	
$t_{gt}$	(note 1)	TYP.	3				$\mu\text{s}$	

(1) Reference test circuit in figure 10 and waveform in figure 11;  $C_T = 0.1\mu\text{F}$  with  $0.1\mu\text{s}$  rise time.  
Note: xx = voltage

### Trigger DIAC Specifications

Symbol	Test Conditions		Value	Unit
$\Delta V_{BO}$	Breakover Voltage Symmetry	MAX.	3	V
$V_{BO}$	Breakover Voltage, forward and reverse	MIN.	33	V
		MAX.	43	
$[\Delta V_{\pm}]$	Dynamic Breakback Voltage, forward and reverse (note 1)	MIN.	5	V
$I_{BO}$	Peak Breakover Current	MAX.	25	$\mu A$
$C_T$	Trigger Firing Capacitance	MAX.	0.1	$\mu F$

(1) Reference test circuit in figure 10 and waveform in figure 11.

### Static Characteristics

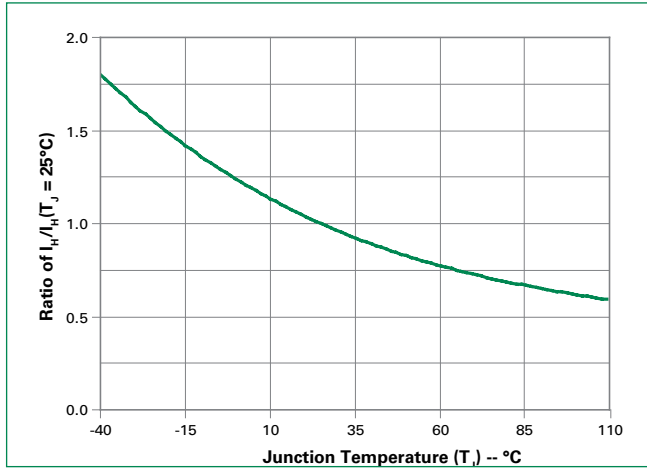
Symbol	Test Conditions		Value	Unit
$V_{TM}$	$I_T = 1.41 \times I_{T(rms)} A; t_p = 380\mu s$	MAX.	1.6	V
$I_{DRM} / I_{RRM}$	$V_{DRM} / V_{RRM}$	$T_J = 25^\circ C$	MAX.	10
		$T_J = 100^\circ C$		500
		$T_J = 125^\circ C$		2000

### Thermal Resistances

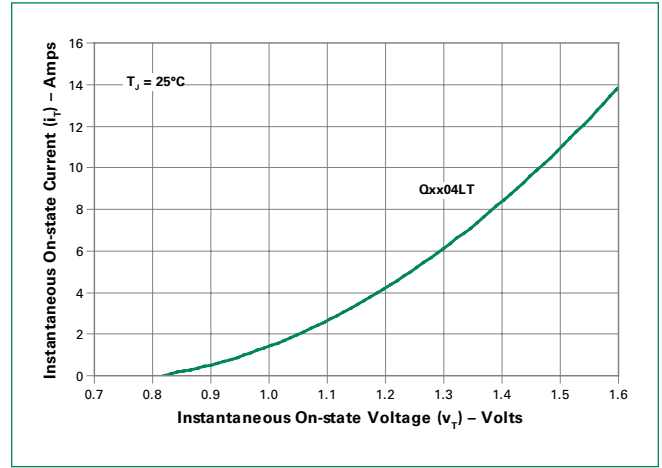
Symbol	Parameter		Value	Unit
$R_{\theta(J-C)}$	Junction to case (AC)	Qxx04LT	3.6	$^\circ C/W$
		Qxx06LT / Qxx06LTH	3.3	
		Qxx08LT / Qxx08LTH	2.8	
		Qxx10LT / Qxx10LTH	2.6	
		Qxx15LT / Qxx15LTH	2.1	
$R_{\theta(J-A)}$	Junction to ambient		50	$^\circ C/W$

Note : xx = voltage

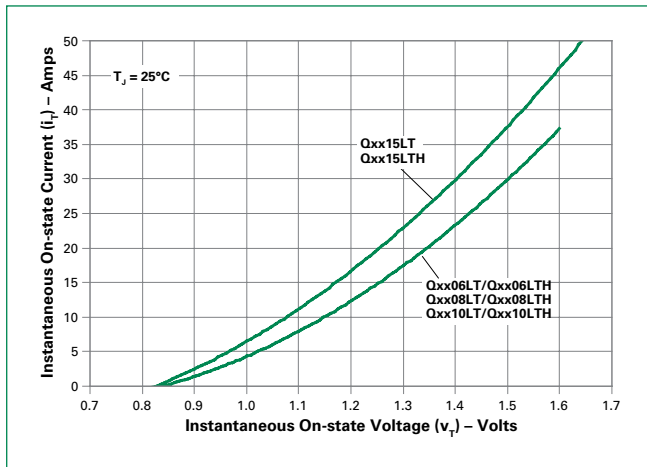
**Figure 1: Normalized DC Holding Current vs. Junction Temperature**



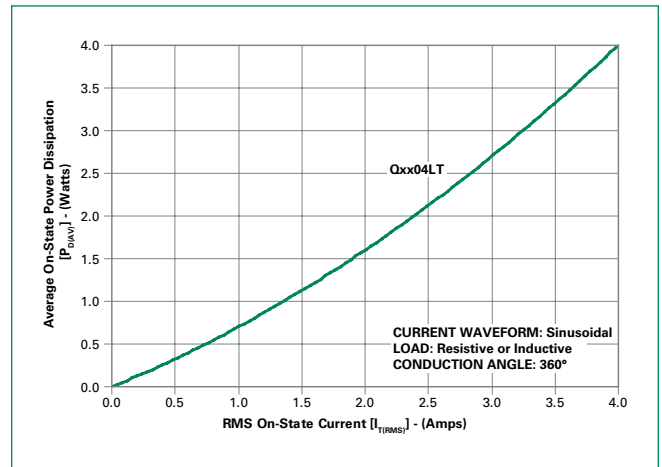
**Figure 2: On-State Current vs. On-State Voltage (Typical) (4A)**



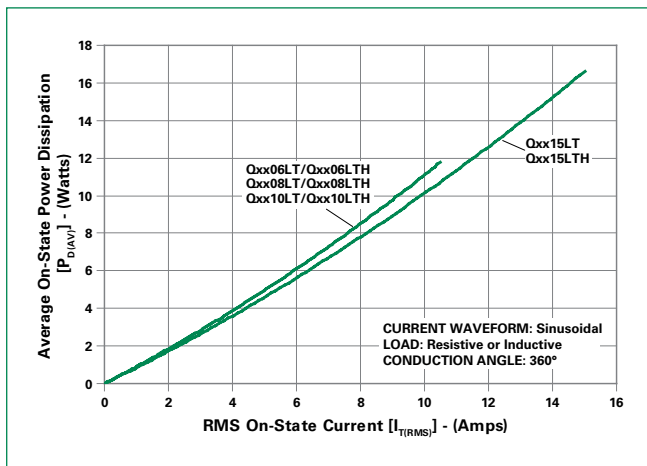
**Figure 3: On-State Current vs. On-State Voltage (Typical) (6A to 15A)**



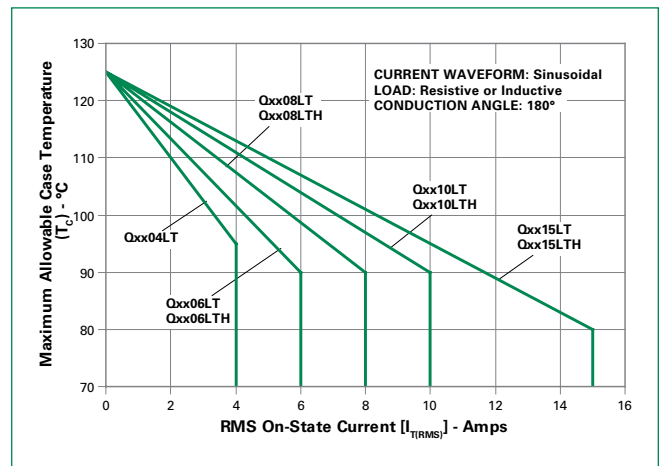
**Figure 4: Power Dissipation vs. RMS On-State Current (Typical) (4A)**



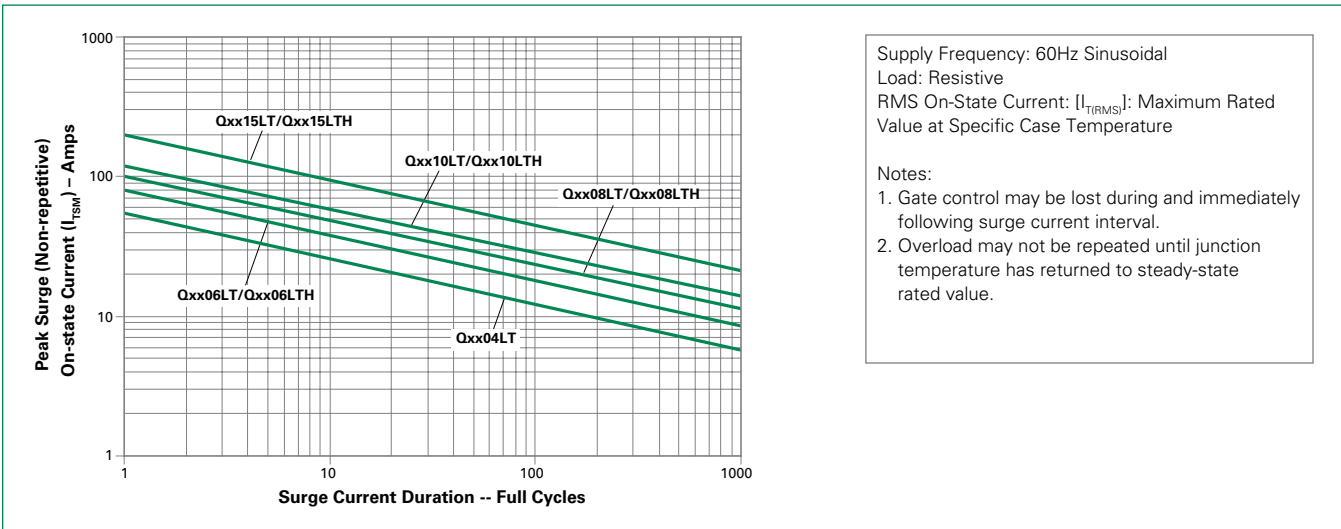
**Figure 5: Power Dissipation vs. RMS On-State Current (Typical) (6A to 15A)**



**Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current**

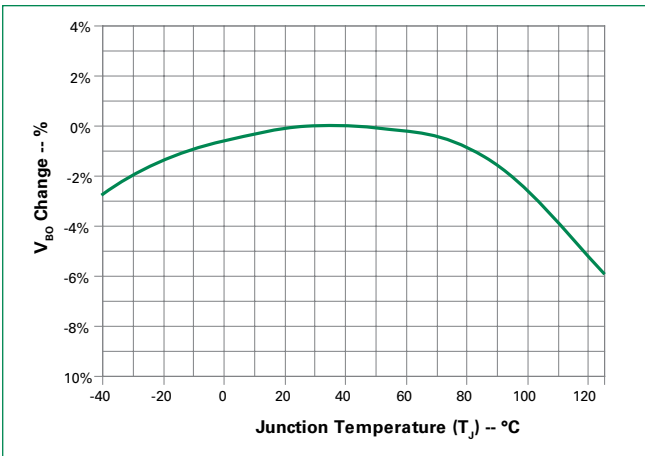


**Figure 7: Surge Peak On-State Current vs. Number of Cycles**

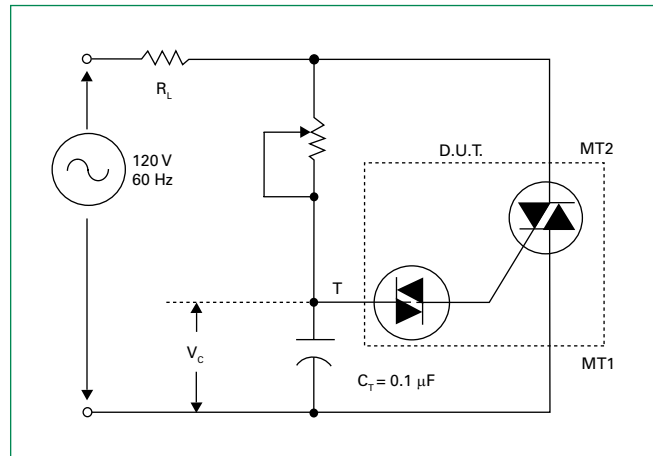


Note: xx = voltage

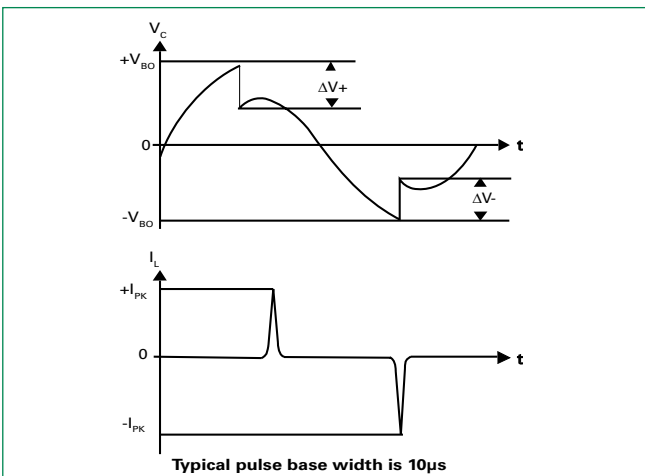
**Figure 8: DIAC  $V_{BO}$  Change vs. Junction Temperature**



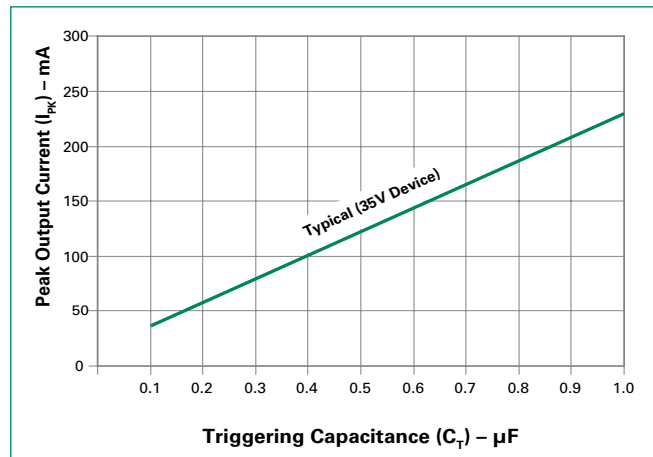
**Figure 9: Test Circuit**



**Figure 10: Test Circuit Waveform**

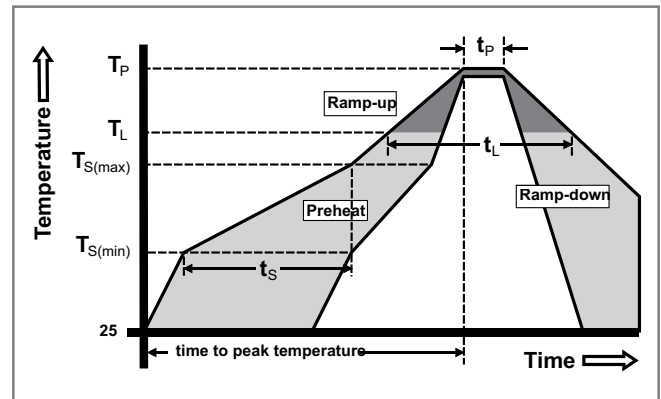


**Figure 11: Peak Output Current vs Triggering Capacitance (Per Figure 9)**



### Soldering Parameters

Reflow Condition		Pb – Free assembly
Pre Heat	- Temperature Min ( $T_{s(min)}$ )	150°C
	- Temperature Max ( $T_{s(max)}$ )	200°C
	- Time (min to max) ( $t_s$ )	60 – 180 secs
Average ramp up rate (Liquidus Temp) ( $T_L$ ) to peak		5°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		5°C/second max
Reflow	- Temperature ( $T_L$ ) (Liquidus)	217°C
	- Temperature ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes Max.
Do not exceed		280°C



### Physical Specifications

<b>Terminal Finish</b>	1005 Matte Tin-plated
<b>Body Material</b>	UL Recognized epoxy meeting flammability classification 94v-0
<b>Lead Material</b>	Copper Alloy

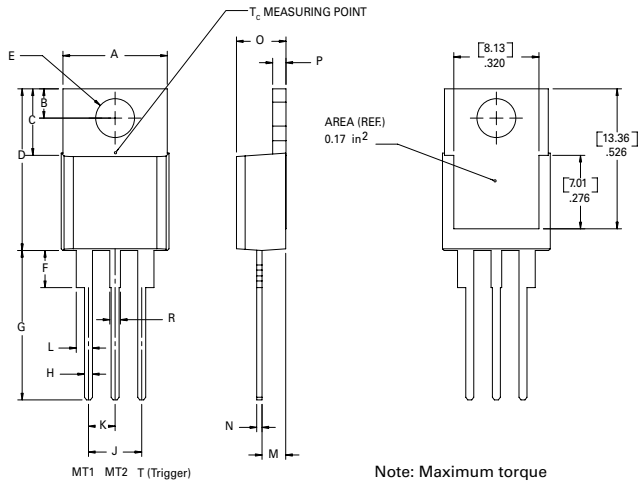
### Design Considerations

Careful selection of the correct device for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the device rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including  $dv/dt$ ), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### Environmental Specifications

Test	Specifications and Conditions
<b>High Temperature Voltage Blocking</b>	MIL-STD-750: Method 1040, Condition A Rated $V_{DRM}$ (VAC-peak), 125°C, 1008 hours
<b>Temperature Cycling</b>	MIL-STD-750: Method 1051 -40°C to 150°C, 15-minute dwell, 100 cycles
<b>Biased Temperature &amp; Humidity</b>	EIA/JEDEC: JESD22-A101 320VDC, 85°C, 85%RH, 1008 hours
<b>High Temp Storage</b>	MIL-STD-750: Method 1031 150°C, 1008 hours
<b>Low-Temp Storage</b>	-40°C, 1008 hours
<b>Thermal Shock</b>	MIL-STD-750: Method 1056 0°C to 100°C, 5-minute dwell, 10-second transfer, 10 cycles
<b>Autoclave (Pressure Cooker Test)</b>	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 2atm, 168 hours
<b>Resistance to Solder Heat</b>	MIL-STD-750: Method 2031 260°C, 10 seconds
<b>Solderability</b>	ANSI/J-STD-002, Category 3, Test A
<b>Lead Bend</b>	MIL-STD-750: Method 2036, Condition E

**Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab**



Note: Maximum torque to be applied to mounting tab is 8 in-lbs. (0.904 Nm).

Dimension	Inches		Millimeters	
	Min	Max	Min	Max
A	0.380	0.420	9.65	10.67
B	0.105	0.115	2.67	2.92
C	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
E	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
H	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
M	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
O	0.178	0.188	4.52	4.78
P	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

**Product Selector**

Part Number	Voltage				Type	Package
	400V	600V	800V	1000V		
Qxx04LT	X	X			Quadrac	TO-220L
Qxx06LT	X	X			Quadrac	TO-220L
Qxx06LTH	X	X			Alternistor Quadrac	TO-220L
Qxx08LT	X	X			Quadrac	TO-220L
Qxx08LTH	X	X			Alternistor Quadrac	TO-220L
Qxx10LT	X	X			Quadrac	TO-220L
Qxx10LTH	X	X			Alternistor Quadrac	TO-220L
Qxx15LT	X	X			Quadrac	TO-220L
Qxx15LTH	X	X			Alternistor Quadrac	TO-220L

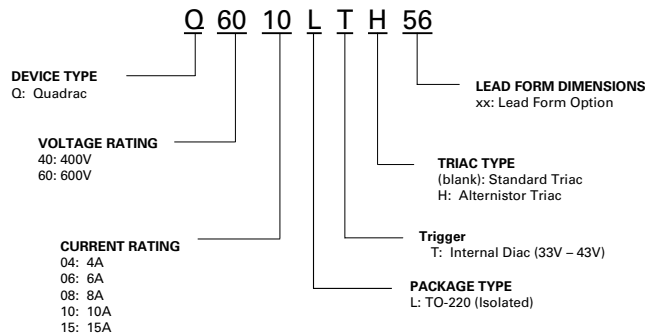
Note: xx = Voltage

### Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Qxx04LT	Qxx04LT	2.2 g	Bulk	500
Qxx04LTPP	Qxx04LT	2.2 g	Tube	500 (50 per tube)
Qxx06LT	Qxx06LT	2.2 g	Bulk	500
Qxx06LTPP	Qxx06LT	2.2 g	Tube	500 (50 per tube)
Qxx06LTH	Qxx06LTH	2.2 g	Bulk	500
Qxx06LTHPP	Qxx06LTH	2.2 g	Tube	500 (50 per tube)
Qxx08LT	Qxx08LT	2.2 g	Bulk	500
Qxx08LTPP	Qxx08LT	2.2 g	Tube	500 (50 per tube)
Qxx08LTH	Qxx08LTH	2.2 g	Bulk	500
Qxx08LTHPP	Qxx08LTH	2.2 g	Tube	500 (50 per tube)
Qxx10LT	Qxx10LT	2.2 g	Bulk	500
Qxx10LTPP	Qxx10LT	2.2 g	Tube	500 (50 per tube)
Qxx10LTH	Qxx10LTH	2.2 g	Bulk	500
Qxx10LTHPP	Qxx10LTH	2.2 g	Tube	500 (50 per tube)
Qxx15LT	Qxx15LT	2.2 g	Bulk	500
Qxx15LTPP	Qxx15LT	2.2 g	Tube	500 (50 per tube)
Qxx15LTH	Qxx15LTH	2.2 g	Bulk	500
Qxx15LTHPP	Qxx15LTH	2.2 g	Tube	500 (50 per tube)

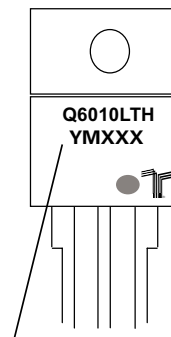
Note: xx = Voltage

### Part Numbering System



### Part Marking System

TO-220 AB - (L Package)



**Date Code Marking**  
Y: Year Code  
M: Month Code  
XXX: Lot Trace Code

# Mouser Electronics

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